

InP S dope 3" wafer



Parameter	Customer's Requirements	UOM
Material	InP	
Growth Method	VGF	
Conduct Type	SI	
Dopant	Fe	
Diameter	76.2±0.4	mm
Orientation	(100)±0.2°	°
Orientation Angle	N/A	
OF Location/Length	EJ (0-1-1) ±0.1° / N/A	mm
IF Location/Length	EJ (0-11) / N/A	mm
Ingot CC	Min: N/A Max: N/A	/cm ³
Resistivity	Min: 5.00E+06 Max: N/A	Ω.cm
Mobility	Min: 1500 Max: N/A	/cm ² /v.s
EPD	Ave: <5000	/cm ²
Thickness	Min: 580 Max: 620	μm
Edge Rounding	N/A	mmR
Laser Marking	N/A	
TTV/TIR	Max: 9.99	μm
BOW	Max: 4.99	μm
Warp	Max: 8	μm
Surface Finish-front	Polished	
Surface Finish-Back	Polished	
Particle Count	≤40/wafer@>0.3μm	
Epi-Ready	N/A	